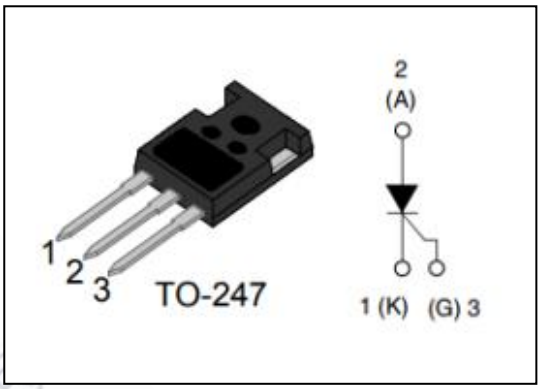
isc Thyristors 40TPS08A

DESCRIPTION

- Long-term stability
- Thyristor for line frequency
- Planar passivated chip
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage		1200	V
V_{RRM}	Repetitive peak reverse voltage		1200	V
$I_{T(AV)}$	Average forward current	@Tc=79℃	35	A
$I_{T(RMS)}$	RMS on-state current		55	A
I_{TSM}	Surge non-repetitive on-state current @tp=10ms		500	A
$P_{G(AV)}$	Average gate power dissipation		1	W
T_j	Operating junction temperature		-40~125	℃
T_{stg}	Storage temperature		-40~150	℃

ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_{RM}=V_{RRM}	T_j=25℃		0.5	mA
I_{DRM}	Repetitive peak off-state current	V_{DM}=V_{DRM}	T_j=125℃		10	
V_{TM}	On-state voltage	I_{TM}= 110A			1.85	V
I_{GT}	Gate-trigger current	V_D=12V R_L=33Ω			150	mA
V_{GT}	Gate-trigger voltage	V_D=12V R_L=33Ω			2.5	V
$R_{th(j-c)}$	Thermal resistance	Junction to case			0.6	℃/W

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